Amendments to the Claims

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

- 1. (Currently Amended) A mixture for etching a dielectric material in a layered substrate, the mixture comprising:
 - a fluorocarbon; and
- a fluorine-containing oxidizer selected from the group consisting of a hypofluorite, a fluoroperoxide, a fluorotrioxide, and combinations thereof, wherein the mixture has a ratio by volume of the fluorine-containing oxidizer to the fluorocarbon from 0.1:1 to 20:1.
 - 2. (Original) The mixture of claim 1 further comprising an inert diluent gas.
- (Original) The mixture of claim 2 wherein the inert diluent gas is at least one selected from the group consisting of argon, neon, xenon, helium, nitrogen, krypton, and combinations thereof.
- 4. (Original) The mixture of claim 2 wherein the mixture comprises from 0.1 to 99% by volume of the inert diluent gas.
- 5. (Original) The mixture of claim 1 wherein the fluorocarbon is at least one selected from the group consisting of perfluorocarbon, hydrofluorocarbon, oxyhydrofluorocarbon, oxyfluorocarbon, and combinations thereof.
- 6. (Original) The mixture of claim 5 wherein the fluorocarbon is at least one perfluorocarbon selected from the group consisting of tetrafluoromethane, trifluoromethane, octafluorocyclopentene, hexafluoro-1,3-butadiene, and combinations thereof.

- 7. (Original) The mixture of claim 6 wherein the perfluorocarbon is hexafluoro-1,3-butadiene.
- 8. (Original) The mixture of claim 5 wherein the fluorocarbon is at least one hydrofluorocarbon.
- 9. (Original) The mixture of claim 9 wherein the fluorocarbon is at least one oxyhydrofluorocarbon.
- 10. (Original) The mixture of claim 5 wherein the oxyhydrofluorocarbon is at least one selected from the group consisting of perfluorocyclopentene oxide, hexafluorocyclobutanone, hexafluorodihydrofuran, hexafluorobutadiene epoxide, tetrafluorocyclobutanedione perfluorotetrahydrofuran (C_4F_8O), hexafluoropropylene oxide (C_3F_6O), perfluoromethylvinyl ether (C_3F_6O), and combinations thereof.
- 11. (Original) The mixture of claim 1 wherein the fluorine-containing oxidizer is a hypofluorite having the formula $C_xH_yF_z(OF)_nO_m$ wherein x is a number ranging from 0 to 8, y is a number ranging from 0 to 17, z is a number ranging from 0 to 17, n is 1 or 2, and m is 0, 1, or 2.
- 12. (Original) The mixture of claim 1 wherein the fluorine-containing oxidizer is a fluoroperoxide selected from the group consisting of difluoro-peroxide, fluoro-trifluoromethyl-peroxide, bis-trifluoromethyl-peroxide, pentafluoroethyl-trifluoromethyl-peroxide, bis-pentafluoroethyl-peroxide, difluorodioxirane, bis-trifluoromethyl peroxydicarbonate, fluoroformyl trifluoromethyl peroxide, bis-fluoroformyl-peroxide, and combinations thereof.
- 13. (Original) The mixture of claim 1 wherein the fluorine-containing oxidizer is a fluorotrioxide selected from the group consisting of bis-trifluoromethyl-trioxide, fluorotrifluoromethyl-trioxide, fluoroformyl trifluoromethyl-trioxide, and combinations thereof.
 - 14. (Canceled)

- 15. (Canceled)
- 16. (Canceled)
- 17. (Original) The mixture of claim 1 wherein the dielectric material is at least one selected from the group consisting of silicon, silicon-containing compositions, silicon dioxide (SiO₂), undoped silicon glass (USG), doped silica glass, silicon and nitrogen containing materials, organosilicate glass (OSG), organofluoro-silicate glass (OFSG), low dielectric constant materials, polymeric materials, porous low dielectric constant materials, and combinations thereof.
- 18. (Original) A mixture for etching a dielectric material in a layered substrate comprising: a fluorocarbon and a hypofluorite.
- 19. (Original) A mixture for etching a dielectric material in a layered substrate comprising: a fluorocarbon and a fluoroperoxide.
- 20. (Original) A mixture for etching a dielectric material in a layered substrate comprising: a fluorocarbon and a fluorotrioxide.

21 to 26. (Canceled)